

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional)

SETI-0005

Application Number

Applicant(s)

Gaska et al.

Filing Date

Herewith

Group Art Unit

*EXAMINER

INITIAL

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

"Introduction to Solid State Lighting," A. Zukašaus et al., John Wiley & Sons, Inc., New York (2002), pp. 37-116.

"Improved Characteristics of InGaN Multiple-Quantum-Well Light-Emitting Diode by GaN/AlGaIn Distributed Bragg Reflector Grown on Sapphire," N. Nakada et al., Applied Physics Letters, Vol. 76, No. 14, April 3, 2000, pp. 1804-1806.

"AlGaIn Single-Quantum-Well Light Emitting Diodes With Emission at 285 nm," V. Adivarahan et al., Applied Physics Letters, Vol. 81, No. 19, November 4, 2002, pp. 3666-3668.

"Strain Energy Band Engineering Approach to AlN/GaN/InN Heterojunction Devices," A. Khan et al., Frontiers in Electronics: Future Chips Proceedings of the 2002 Workshop on Frontiers in Electronics (Wofe-02) St. Croix, Virgin Islands, World Scientific Pub Co; (January 15, 2003), ISBN: 9812382224, Vol. 26. Series Selected Topics in Electronics and Systems, pp. 195-214.

"A Vertical Injection Blue Light Emitting Diode in Substrate Separated InGaIn Heterostructures," Y. -K. Song et al., Applied Physics Letters, Vol. 74, no. 24, June 14, 1999, pp. 3720-3722.

EXAMINER

DATE CONSIDERED

01/10/2005

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.